

描述 / Descriptions

PDFN3×3-8L 塑封封装双 N 沟道 MOS 场效应管。

Double N-CHANNEL MOSFET in a PDFN3×3-8L Plastic Package.

特征 / Features

$V_{DS}=40V$ $I_D=19A$

$R_{DS(ON)}@10V<20m\Omega$ (Typ.18mR)

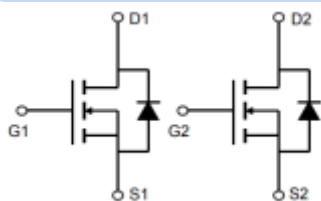
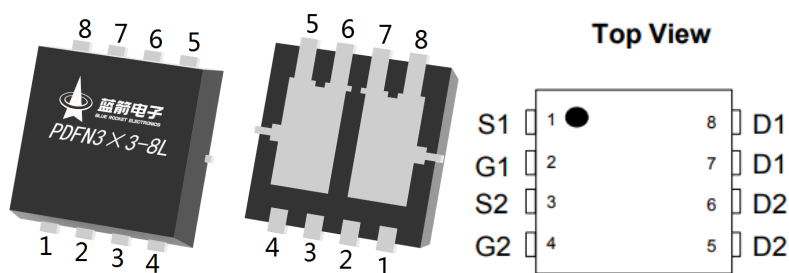
$R_{DS(ON)}@4.5V<35m\Omega$ (Typ.24mR)

无卤产品。HF Product.

用途 / Applications

同步整流，DC/DC 转换器。

Synchronous Rectification,DC/DC Converter.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning****印章代码 / Marking**

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	40	V
Drain Current		$I_D(T_c=25^{\circ}\text{C})$	19	A
Drain Current - Pulsed		I_{DM}	38	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25^{\circ}\text{C})$	12	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Junction-to-Ambient	Steady-State	$R_{\theta JA}$	95	$^{\circ}\text{C/W}$
Junction-to-Case	Steady-State	$R_{\theta JC}$	10.4	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	40	45		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V$ $V_{GS}=0V$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1	1.8	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=6.0A$		18	20	m Ω
		$V_{GS}=4.5V$ $I_D=5.0A$		24	35	m Ω
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1200		pF
Output Capacitance	C_{oss}			350		pF
Reverse Transfer Capacitance	C_{rss}			250		pF
Gate resistance	R_g	$V_{DS}=0V$ $f=1.0MHz$ $V_{GS}=0V$		2.5		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=6A$		9.2		nC
Total Gate Charge	$Q_{g(4.5V)}$			4.5		
Gate-Source Charge	Q_{gs}			2.5		nC
Gate-Drain Charge	Q_{gd}			1.5		nC

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=20V$ $V_{GS}=10V$ $R_L=3.3\Omega$ $R_{GEN}=3\Omega$		6.5		ns
Turn-On Rise Time	t_r			3.7		ns
Turn-Off Delay Time	$t_{d(off)}$			18.2		ns
Turn-Off Fall Time	t_f			7.1		ns

电参数曲线图 / Electrical Characteristic Curve

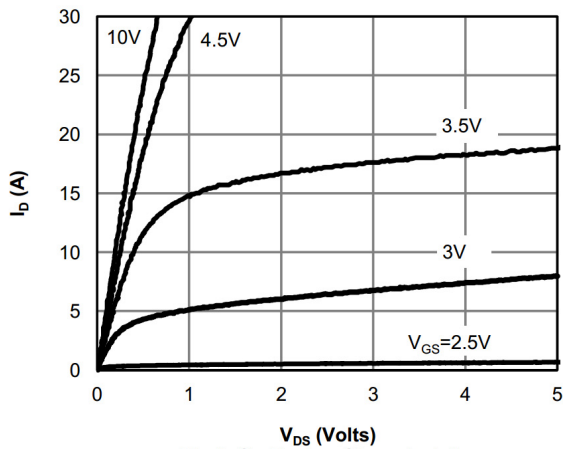


Fig 1: On-Region Characteristics

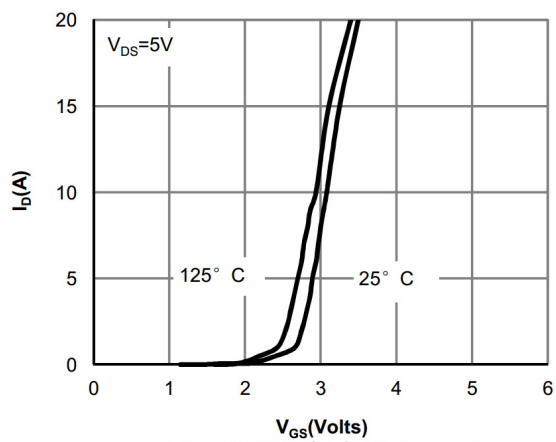


Figure 2: Transfer Characteristics

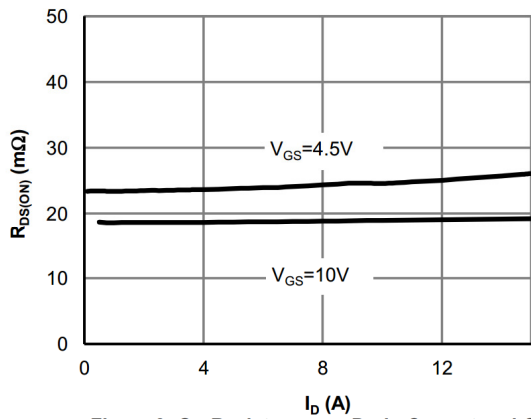


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

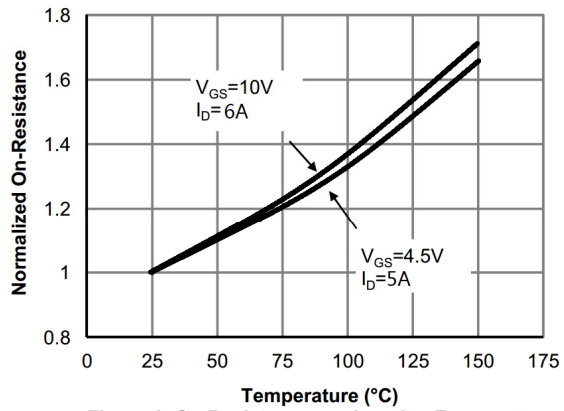


Figure 4: On-Resistance vs. Junction Temperature

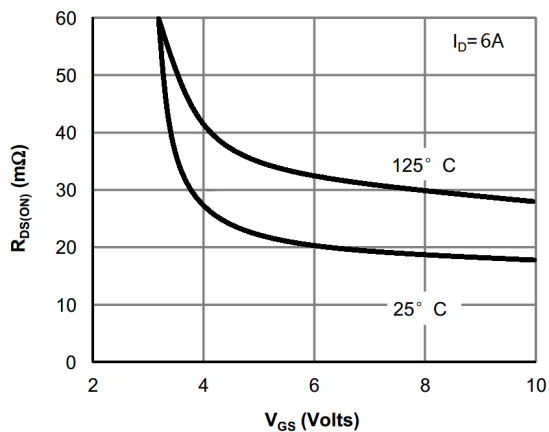


Figure 5: On-Resistance vs. Gate-Source Voltage

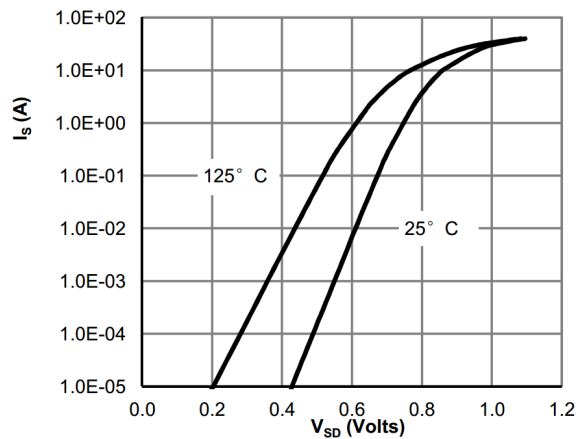
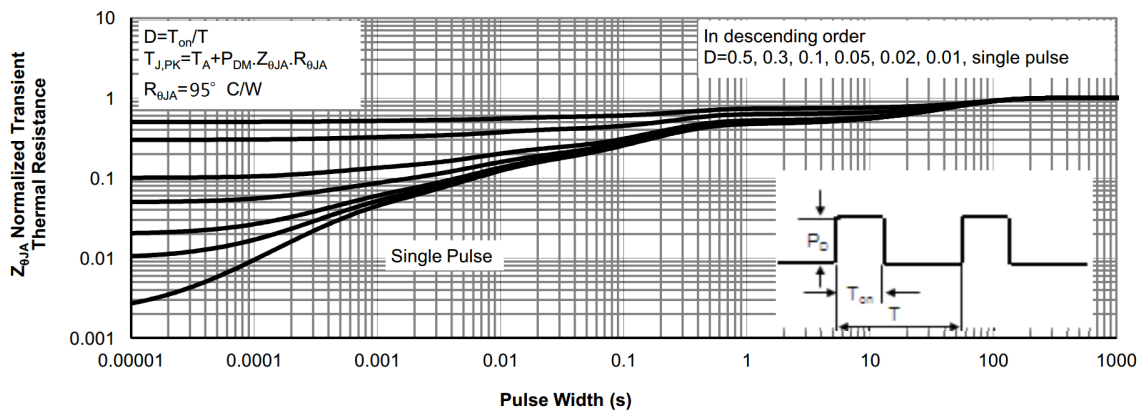
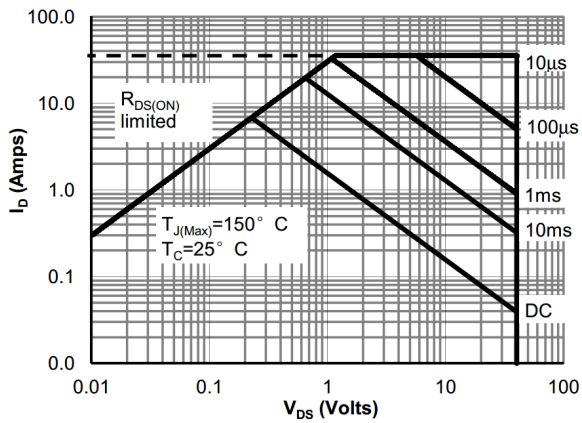
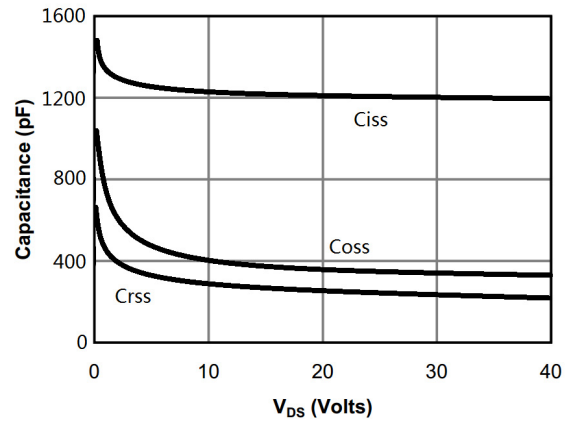
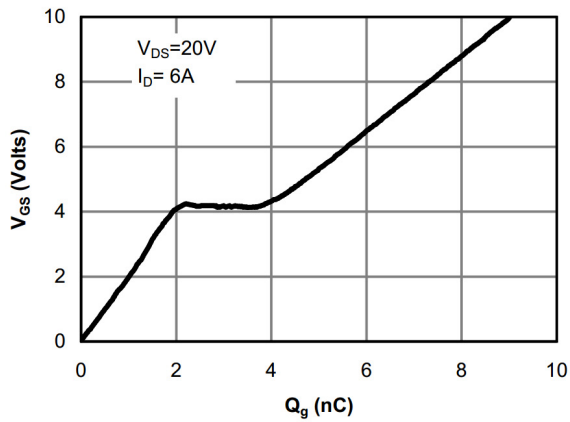


Figure 6: Body-Diode Characteristics

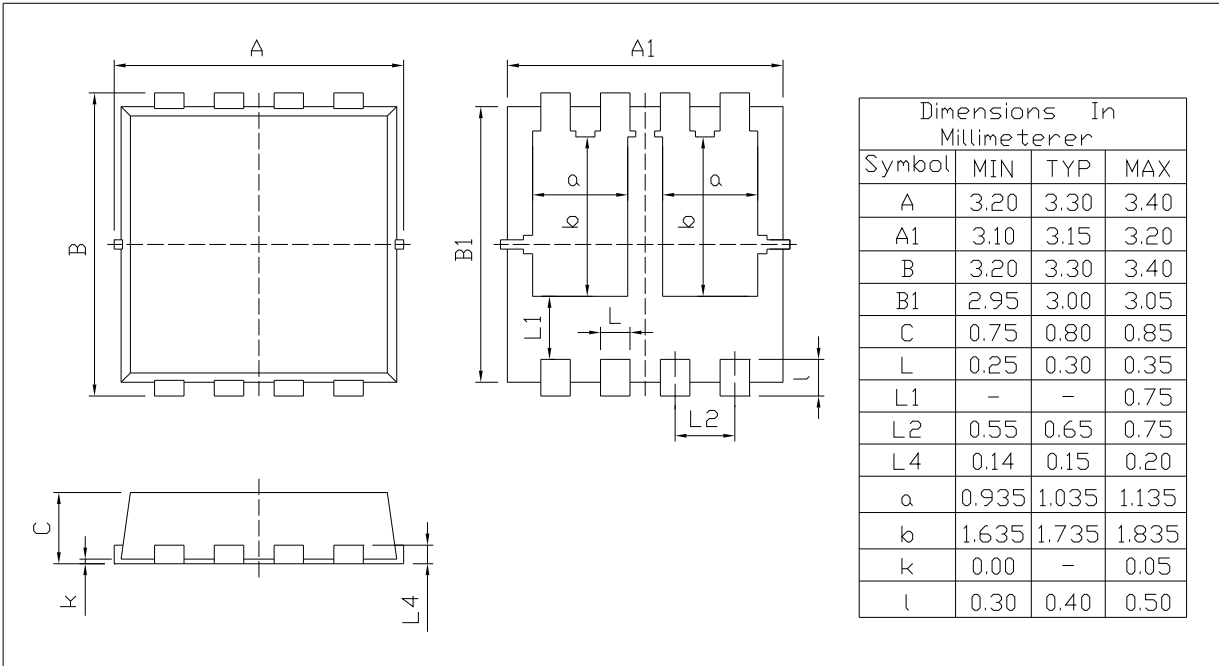
N-沟道电参数曲线图 / N-CHANNEL Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

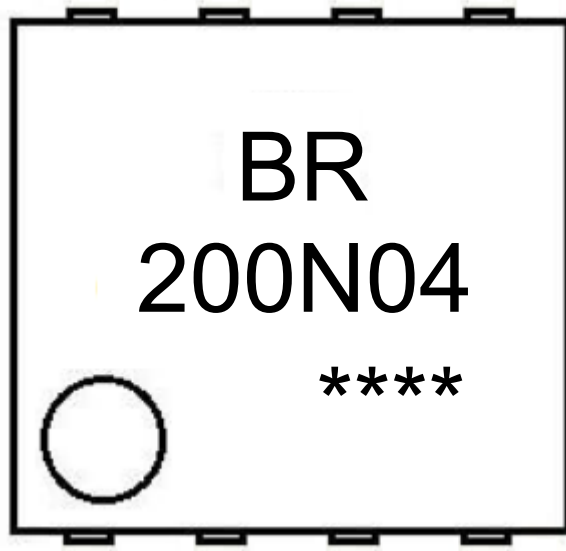
PDFN3X3-8L

Unit:mm



Rev.00 202011

印章说明 / Marking Instructions



说明：

BR： 为公司代码

200N04： 为型号代码

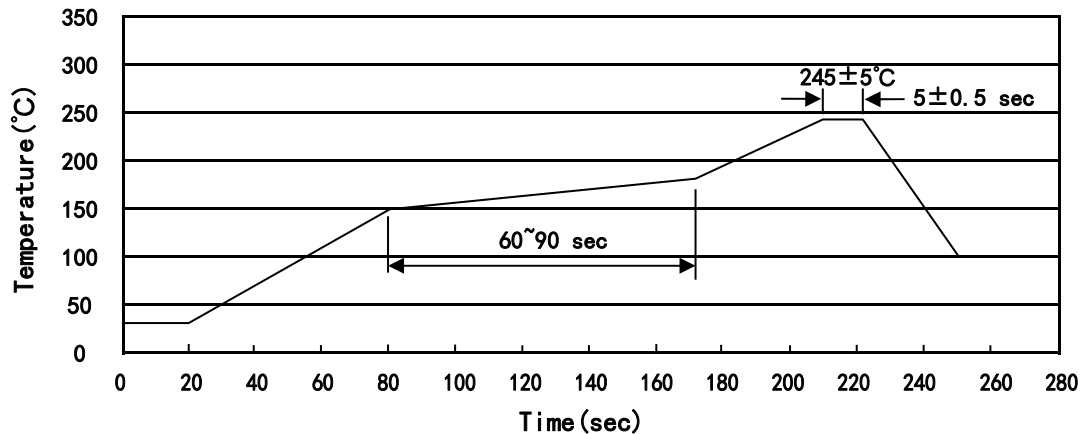
****： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

200N04: Product Type Code

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN3×3-8L	5,000	2	10,000	6	60,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices